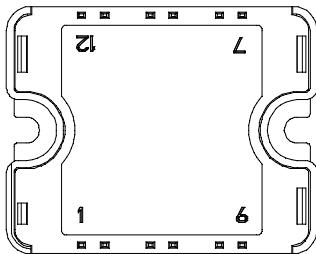
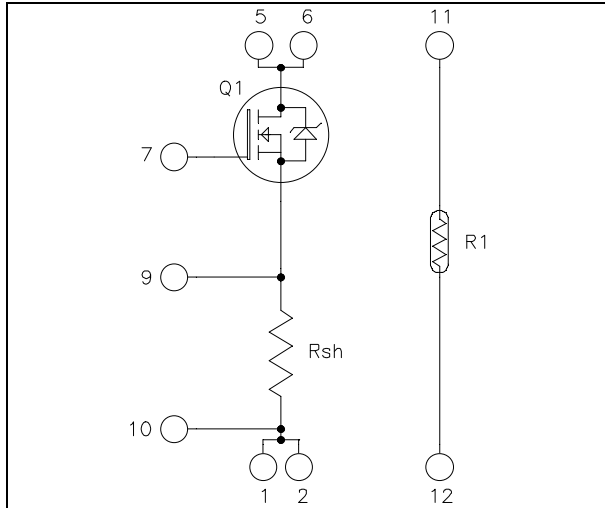


Linear MOSFET Power Module

$$V_{DSS} = 1000V$$

$$R_{DSon} = 600m\Omega \text{ typ @ } T_j = 25^\circ C$$

$$I_D = 20A \text{ @ } T_c = 25^\circ C$$



Pins 1/2 ; 5/6 must be shorted together

Application

- Electronic load dedicated to power supplies and battery discharge testing

Features

- Linear MOSFET
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration
- AlN substrate for improved thermal performance

Benefits

- Direct mounting to heatsink (isolated package)
- easy series and parallels combinations for power and voltage improvements
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1000	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	20
		$T_c = 80^\circ C$	14
I_{DM}	Pulsed Drain current	74	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	720	m Ω
P_D	Maximum Power Dissipation ❶	$T_c = 25^\circ C$	520
			W

❶ In saturation mode

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1000\text{V}$; $V_{GS} = 0\text{V}$ $T_j = 25^\circ\text{C}$			250	μA
		$V_{DS} = 800\text{V}$; $V_{GS} = 0\text{V}$ $T_j = 125^\circ\text{C}$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}$, $I_D = 10\text{A}$		600	720	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 2.5\text{mA}$	2		4	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		6000		pF
C_{oss}	Output Capacitance			775		
C_{rss}	Reverse Transfer Capacitance			285		

Shunt Electrical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
R_{sh}	Resistance value		20		$\text{m}\Omega$
T_{sh}	Tolerance		2		%
P_{sh}	Load capacity	$T_C = 25^\circ\text{C}$		20	W
		$T_C = 80^\circ\text{C}$		10	
I_{sh}	Current capacity	$T_C = 25^\circ\text{C}$		31	A
		$T_C = 80^\circ\text{C}$		22	

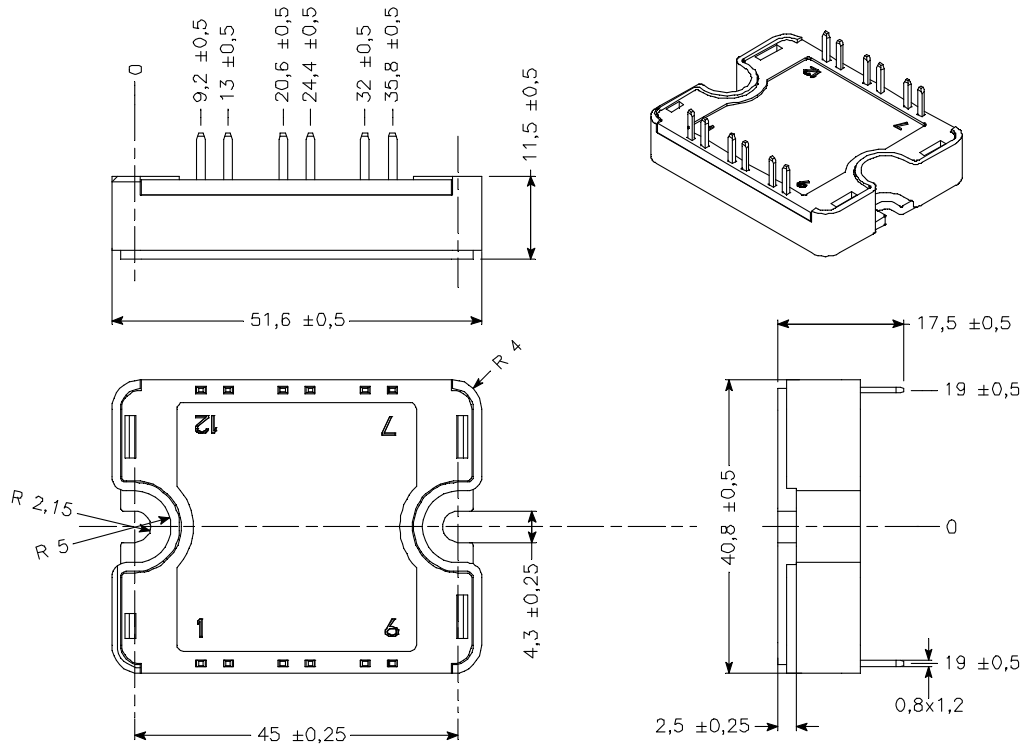
Temperature sensor PTC

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C	1980		2020	Ω
R_{100}/R_{25}	Resistance ratio	$T_{amb} = 100^\circ\text{C}$ & 25°C	1.676	1.696	1.716
R_{55}/R_{25}	Resistance ratio	$T_{amb} = -55^\circ\text{C}$ & 25°C	0.48	0.49	0.50
B	Temperature coefficient		7900		ppm/K

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance		MOSFET			0.24	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2.5		4.7	N.m
Wt	Package Weight					80	g

SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.